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FDMB2307NZ

Dual Common Drain N-Channel PowerTrench® MOSFET 20 V, 9.7 A, 16.5 m Ω

Features

- Max $r_{S1S2(on)} = 16.5 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_D = 8 \text{ A}$
- Max $r_{S1S2(on)} = 18 \text{ m}\Omega$ at $V_{GS} = 4.2 \text{ V}$, $I_D = 7.4 \text{ A}$
- Max $r_{S1S2(on)} = 21 \text{ m}\Omega$ at $V_{GS} = 3.1 \text{ V}$, $I_D = 7 \text{ A}$
- Max $r_{S1S2(on)}$ = 24 m Ω at V_{GS} = 2.5 V, I_D = 6.7 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x3 mm
- HBM ESD protection level > 2 kV (Note 3)
- RoHS Compliant

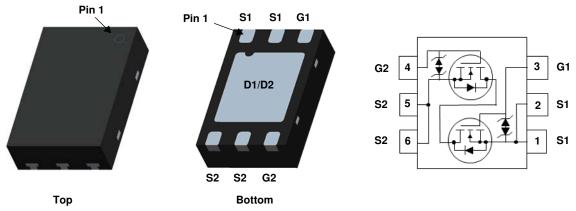
General Description

This device is designed specifically as a single package solution for Li-lon battery pack protection circuit and other ultra-portable applications. It features two common drain N-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced PowerTrench® process with state of the art MicroFET Leadframe, the FDMB2307NZ minimizes both PCB space and $r_{\rm S1S2(on)}.$

Application

■ Li-Ion Battery Pack





MLP 2x3

MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{S1S2}	Source1 to Source2 Voltage			20	V
V _{GS}	Gate to Source Voltage		(Note 4)	±12	V
1	Source1 to Source2 Current -Continuous	T _A = 25°C	(Note 1a)	9.7	^
IS1S2	-Pulsed			40	Α
D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.2	w
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1b)	0.8	VV
T _J , T _{STG}	Operating and Storage Junction Temperature	Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(Dual Operation)	(Note 1a)	57	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(Dual Operation)	(Note 1b)	161	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
307	FDMB2307NZ	MLP 2x3	7"	8 mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
I _{S1S2}	Zero Gate Voltage Source1 to Source2 Current	V _{S1S2} = 16 V, V _{GS} = 0 V			1	μА
I _{GSS}	Gate to Source Leakage Current	V _{GS} = 12 V, V _{S1S2} = 0 V			10	μА

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{S1S2}, I_{S1S2} = 250 \mu A$	0.6	1	1.5	V
r _{S1S2(on)} Static Source1 to Source2 On Resistance	V _{GS} = 4.5 V, I _{S1S2} = 8 A	10.5	13.5	16.5		
	V _{GS} = 4.2 V, I _{S1S2} = 7.4 A	11	14	18		
	Static Source1 to Source2 On Resistance	V _{GS} = 3.1 V, I _{S1S2} = 7 A	11.5	16	21	mΩ
	Static Source F to Source2 Of Mesistance	$V_{GS} = 2.5 \text{ V}, I_{S1S2} = 6.7 \text{ A}$	12	18	24	11152
	$V_{GS} = 4.5 \text{ V}, I_{S1S2} = 8 \text{ A},$ $T_{J} = 125 \text{ °C}$	11	20	29		
9 _{FS}	Forward Transconductance	V _{S1S2} = 5 V, I _{S1S2} = 8 A		41		S

Dynamic Characteristics

C _{iss}	Input Capacitance		V 10.V.V 0.V		1760	2640	pF
Coss			$V_{S1S2} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		229	345	pF
C _{rss}	Reverse Transfer Capacitance		1 - 1 1/11/12		211	320	pF
R_g	Gate Resistance	(Note 5)		0.1	2.6	8	Ω

Switching Characteristics

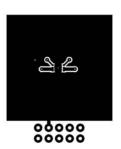
t _{d(on)}	Turn-On Delay Time		12	22	ns
t _r	Rise Time	V _{S1S2} = 10 V, I _{S1S2} = 8 A,	19	34	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 4.5 V, R_{GEN} = 6 Ω	32	51	ns
t _f	Fall Time		9.5	17	ns
Q_g	Total Gate Charge	V _{G1S1} = 0 V to 5 V	20	28	nC
Q_g	Total Gate Charge	$V_{G1S1} = 0 \text{ V to } 4.5 \text{ V}$ $V_{S1S2} = 10 \text{ V}$, $I_{S1S2} = 8 \text{ A}$,	18	25	nC
Q_{gs}	Gate1 to Source1 Charge	$V_{G2S2} = 0 \text{ V}$	2.8		nC
Q_{gd}	Gate1 to Source2 "Miller" Charge	G252 - 0 •	5.3		nC

Source1- Source2 Diode Characteristics

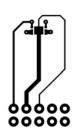
I _{fss}	Maximum Continuous Source1-Source2 Diode Forward Current			8	Α
V _{fss}	Source1 to Source2 Diode Forward Voltage $\begin{vmatrix} V_{G1S 1} = 0 \text{ V}, V_{G2S2} = 4 \\ I_{fss} = 8 \text{ A} \end{vmatrix}$.5 V, (Note 2)	0.8	1.2	٧

NOTES

^{1.} $R_{\theta,JA}$ is determined with the device mounted on a 1 in 2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.



a. 57 °C/W when mounted on
 a 1 in² pad of 2 oz copper



b. 161 °C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.
- 3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.
- 4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse ocurrence only. No continuous rating is implied.
- 5. Rg is measured on 100% of the die at wafer level.

Typical Characteristics T_J = 25°C unless otherwise noted

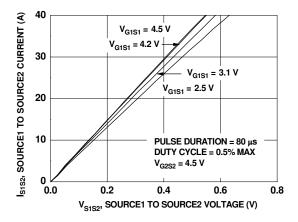


Figure 1. On-Region Characteristics

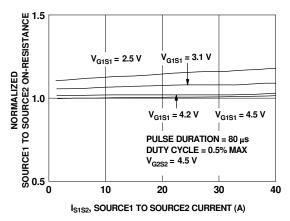


Figure 3. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage

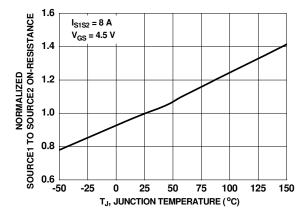


Figure 5. Normalized On Resistance vs Junction Temperature

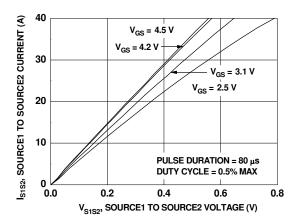


Figure 2. On-Region Characteristics

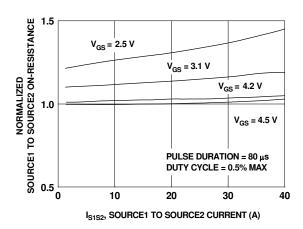


Figure 4. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage

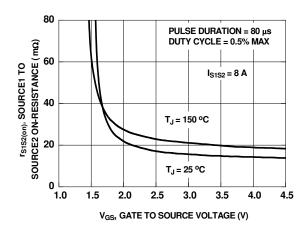


Figure 6. On Resistance vs Gate to Source Voltage

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

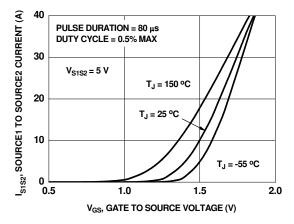


Figure 7. Transfer Characteristics

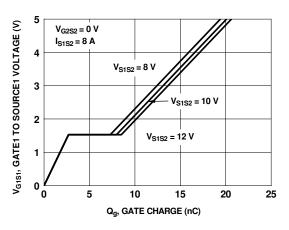
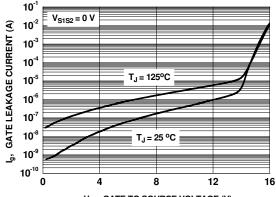
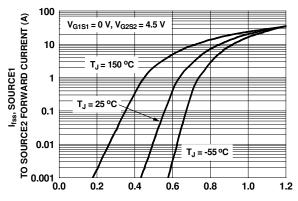


Figure 9. Gate Charge Characteristics



V_{GS}. GATE TO SOURCE VOLTAGE (V)
Figure 11. Gate Leakage Current vs
Gate to Source Voltage



V_{fss}, BODY DIODE FORWARD VOLTAGE (V)

Figure 8. Source1 to Source2 Diode Forward Voltage vs Source Current

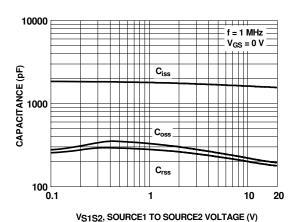


Figure 10. Capacitance vs Source1 to Source2 Voltage

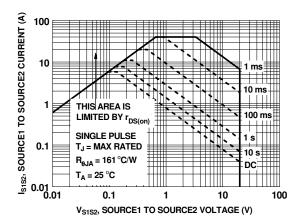


Figure 12. Forward Bias Safe Operating Area

Typical Characteristics T_J = 25°C unless otherwise noted

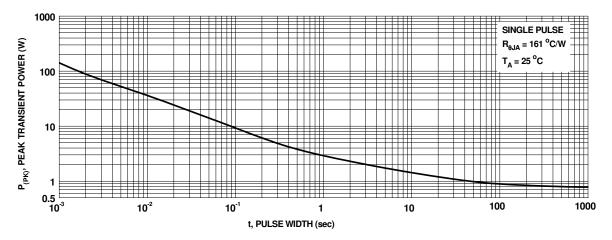


Figure 13. Single Pulse Maximum Power Dissipation

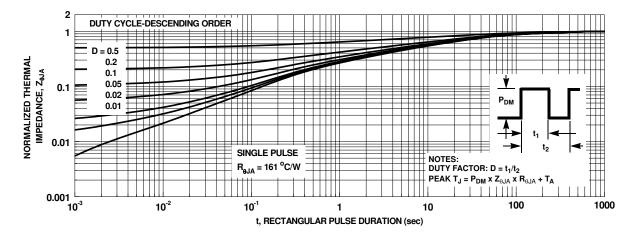
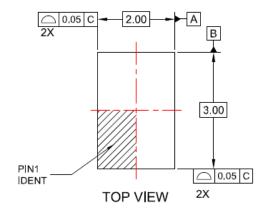
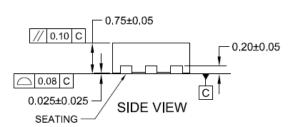
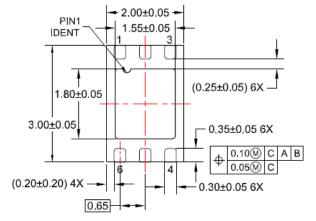


Figure 14. Junction-to-Ambient Transient Thermal Response Curve

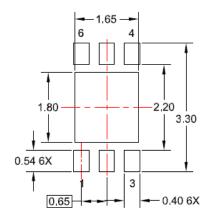
Dimensional Outline and Pad Layout







BOTTOM VIEW



RECOMMENDED LAND PATTERN

NOTES:

- A. PACKAGE CONFORMS TO JEDEC MO-229 EXCEPT WHERE NOTED.
- B. DRAWING FILENAME: MKT-MLP06Qrev3.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
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